

# MBR1535CT MBR1545CT

# SCHOTTKY RECTIFIER

15 Amp

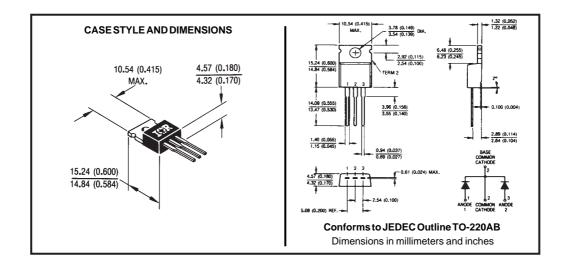
#### **Major Ratings and Characteristics**

Characteristics	MBR15CT	Units
I <sub>F(AV)</sub> Rectangular waveform	15	А
V <sub>RRM</sub>	35/45	V
I <sub>FSM</sub> @ tp=5µssine	690	А
V <sub>F</sub> @ 7.5 Apk, T <sub>J</sub> =125°C	0.57	V
T <sub>J</sub>	-65 to 150	°C

#### **Description/Features**

The MBR15...CT center tap Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150° C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- 150° C T operation
- Center tap TO-220 package
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability



www.irf.com

### MBR1535CT, MBR1545CT

PD-2.318 rev. A 12/97

### Voltage Ratings

Part number	MBR1535CT	MBR1545CT
V <sub>R</sub> Max. DC Reverse Voltage (V)	-	
V <sub>RWM</sub> Max. Working Peak Reverse Voltage (V)	35	45

# Absolute Maximum Ratings

	Parameters	MBR15CT	Units	Conditions
I <sub>F(AV)</sub>	Max.AverageForwardCurrent(PerLeg) (Per Device)	7.5 15	А	@T <sub>C</sub> =105°C,(RatedV <sub>R</sub> )
I <sub>FSM</sub>	Max. Peak One Cycle Non Repetitive Surge	690	7 ^ [	5μs Sine or 3μs Rect. pulse Condition and with rated V <sub>RRM</sub> applied
	Surge	150		Surgeappliedatratedloadconditionhalfwavesingle phase60Hz
I <sub>RRM</sub>	PeakRepetitiveReverseSurgeCurrent	1.0	Α	2.0 µsec 1.0 KHz

## **Electrical Specifications**

	Parameters	MBR15CT	Units	C	Conditions
V <sub>FM</sub>	Max. Forward Voltage Drop	0.84	V	@ 15A	T <sub>J</sub> = 25 °C
	(1)	0.57	V	@ 7.5A	T 425 °C
		0.72	V	@ 15A	T <sub>J</sub> = 125 °C
I <sub>RM</sub>	Max. Instantaneus Reverse Current	0.1	mA	T <sub>J</sub> = 25 °C	Rated DC voltage
	(1)	15	mA	T <sub>J</sub> = 125 °C	Rated DC Voltage
C <sub>T</sub>	Max. Junction Capacitance	400	pF	$V_R = 5V_{DC}$ , (test signal range 100Khz to 1Mhz) 25°C	
L <sub>s</sub>	Typical Series Inductance	8.0	nΗ	Measured from top of terminal to mounting plane	
dv/dt	Max. Voltage Rate of Change (Rated V <sub>R</sub> )	1000	V/ µs		

<sup>(1)</sup> Pulse Width < 300µs, Duty Cycle <2%

### Thermal-Mechanical Specifications

	Parameters		MBR15CT	Units	Conditions
T <sub>J</sub>	Max.JunctionTemperatureR	ange	-65to150	℃	
T <sub>stg</sub>	Max.StorageTemperatureRa	ange	-65to175	℃	
R <sub>thJC</sub>	Max.ThermalResistanceJur toCase	nction	3.0	°C/W	DCoperation
R <sub>thCS</sub>	TypicalThermalResistance, to Heatsink	Case	0.50	°C/W	Mountingsurface, smooth and greased
R <sub>thJA</sub>	Max.ThermalResistanceJunction		60	°C/W	DCoperation
wt	ApproximateWeight		2(0.07)	g(oz.)	
Т	MountingTorque	Min.	6(5)	Kg-cm	
	Max.	Max.	12(10)	(lbf-in)	
	Case Style		TO-220AB		JEDEC

<sup>\*</sup> For Additional Informations and Graphs, Please See the 12CTQ Series

2 www.irf.com